Low VCE (sat) Bipolar Transistor (PNP)NPN, (-)50V, (-)2A

Features

- Adoption of MBIT Process
- Large Current Capacity
- Low Collector to Emitter Saturation Voltage
- High Speed Switching
- Ultrasmall Package Facilitates Miniaturization in End Products (mounting height: 0.9mm)
- High Allowable Power Dissipation

Typical Applications

- Relay Drivers
- Lamp Drivers
- Motor Drivers
- Flash

SPECIFICATIONS (): CPH3145

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Collector to Base Voltage	VCBO	(-50)80	V
Collector to Emitter Voltage	VCES	(-50)80	٧
Collector to Emitter Voltage	VCEO	(-)50	V
Emitter to Base Voltage	VEBO	(-)6	٧
Collector Current	IC	(-)2	Α
Collector Current (Pulse)	ICP	(-)4	Α
Base Current	lΒ	(-)400	mA
Collector Dissipation When mounted on ceramic substrate (600mm² × 0.8mm)	PC	0.9	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

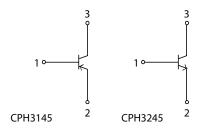
Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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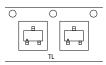
www.onsemi.com

ELECTRICAL CONNECTION PNP NPN

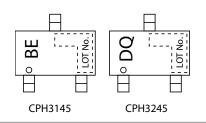


- 1:Base
- 2: Emitter
- 3 : Collector

PACKING TYPE: TL



MARKING



ORDERING INFORMATION

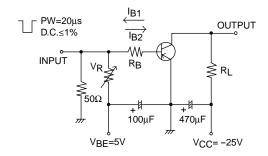
See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

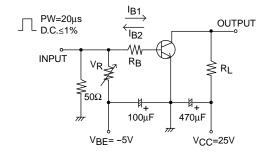
Davarantas	Come had	Conditions	Value			I Incit
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	VCB=(-)40V, IE=0A			(-)1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0A			(-)1	μΑ
DC Current Gain	hFE	V _{CE} =(-)2V, I _C =(-)100mA 2			560	
Gain-Bandwidth Product	fŢ	V _{CE} =(-)10V, I _C =(-)300mA		420		MHz
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(16)8		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)	IC=(-)1A, IB=(-)50mA		(-165)130	(-330)260	mV
Base to Emitter Saturation Voltage	V _{BE} (sat)	.G (), .B ()ee		(-)0.9	(-)1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μA, I _E =0A	(-50)80			٧
Collector to Emitter Breakdown Voltage	V(BR)CES	I _C =(-)100μA, R _{BE} =0Ω	(-50)80			V
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC=(−)1mA, RBE=∞	(–)50			V
Emitter to Base Breakdown Voltage	V(BR)EBO	IE=(-)10μA, IC=0A	(-)6			V
Turn-ON Time	ton			(35)35		ns
Storage Time	t _{stg}	See specified Test Circuit		(200)330		ns
Fall Time	tf			(24)40		ns

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

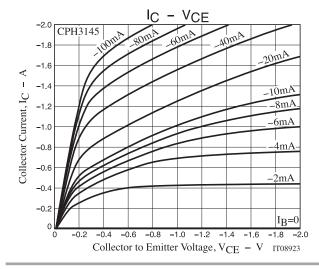
Switching Time Test Circuit

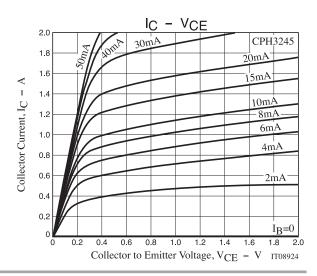


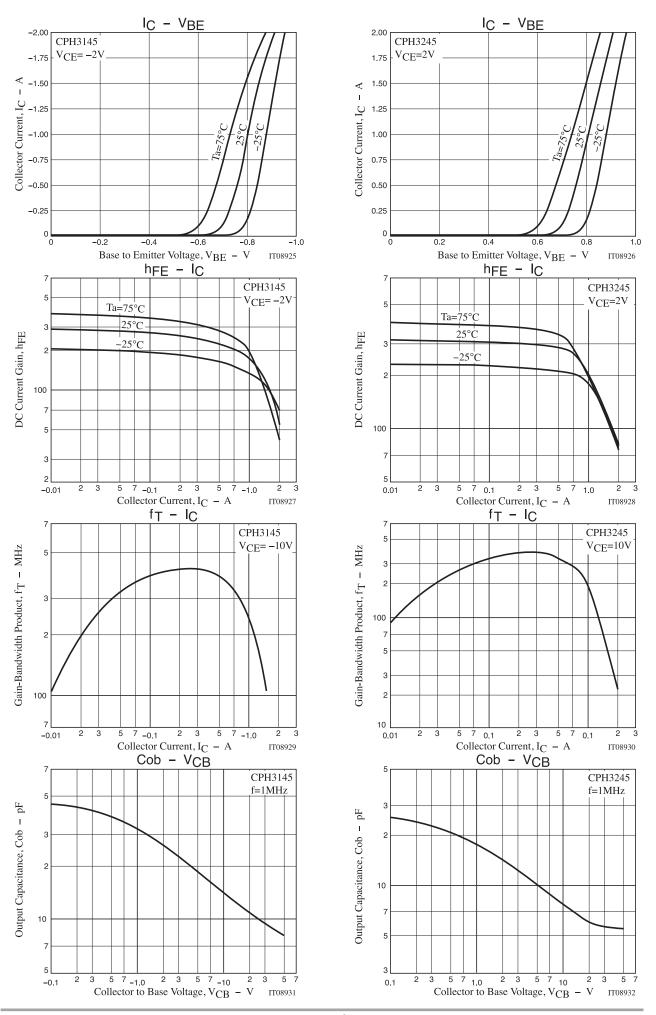
$$I_{C}$$
= $-10I_{B1}$ = $10I_{B2}$ = $-0.7A$

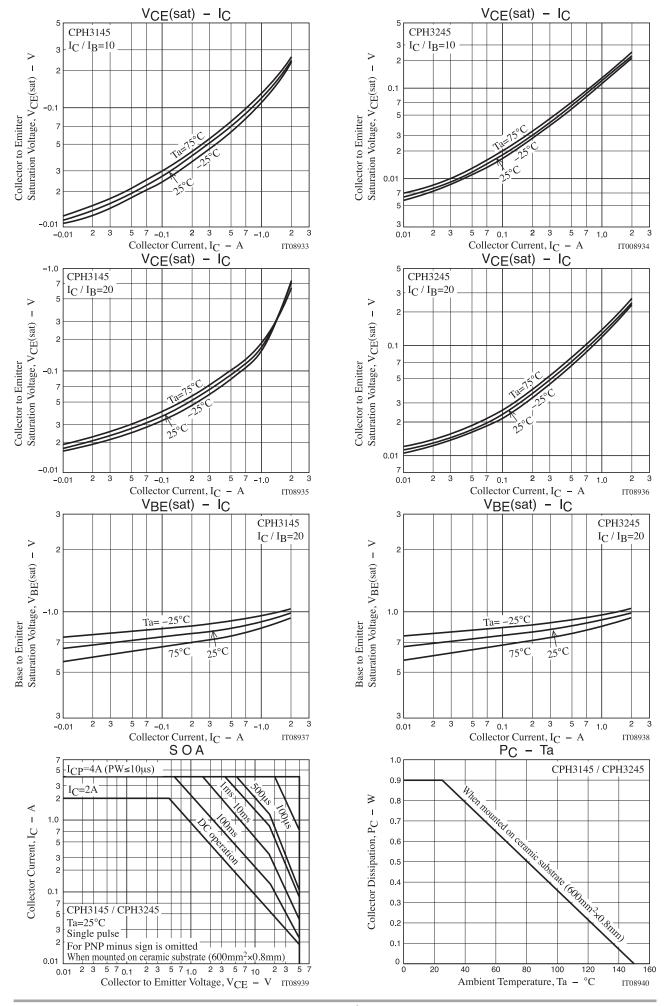


$$I_{C}=10I_{B1}=-10I_{B2}=0.7A$$
 CPH3245



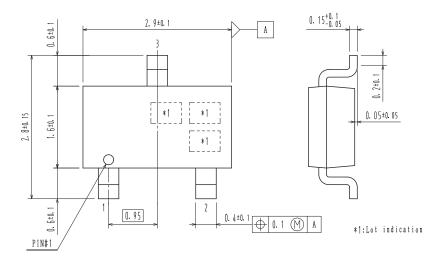






PACKAGE DIMENSIONS

unit: mm CPH3 CASE 318BA ISSUE O



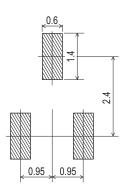
0.0 940.05

1 : Base

2 : Emitter

3 : Collector

Recommended Soldering Footprint



ORDERING INFORMATION

ORDERING IN ORMATION								
Device	Marking	Package	Shipping (Qty / Packing)					
CPH3145-TL-E	BE	CPH3 SC-59, SOT-23, TO-236	3,000 / Tape & Reel					
CPH3245-TL-E	DQ	(Pb-Free)						

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

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